

MITSUBISHI THYRISTOR MODULES

TM15T3A-M,-H

MEDIUM POWER GENERAL USE
INSULATED TYPE

TM15T3A-M,-H



- **I_O** DC output current **30A**
- **V_{RRM}** Repetitive peak reverse voltage **400/800V**
- **V_{DRM}** Repetitive peak off-state voltage **400/800V**
- **3 Phase Mix Bridge**
- **Insulated Type**
- **UL Recognized**

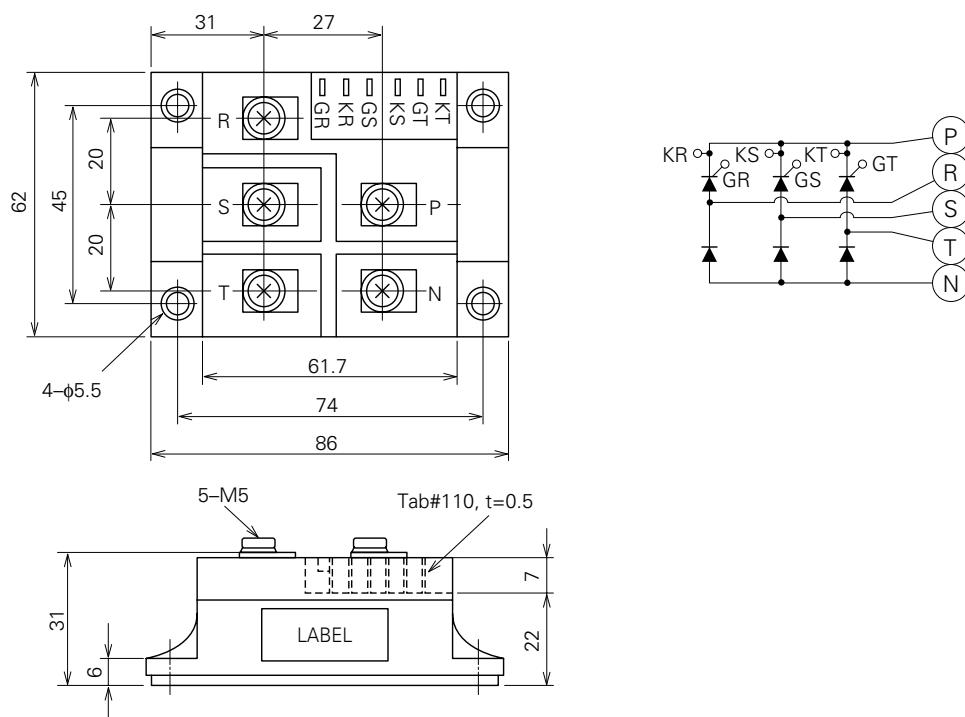
Yellow Card No. E80276 (N)
File No. E80271

APPLICATION

DC motor control, NC equipment, AC motor control, contactless switches, electric furnace temperature control, light dimmers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Feb.1999

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		M	H	
V _{RRM}	Repetitive peak reverse voltage	400	800	V
V _{RSM}	Non-repetitive peak reverse voltage	480	960	V
V _{R (DC)}	DC reverse voltage	320	640	V
V _{DRM}	Repetitive peak off-state voltage	400	800	V
V _{DSM}	Non-repetitive peak off-state voltage	480	960	V
V _{d (DC)}	DC off-state voltage	320	640	V

Symbol	Parameter	Conditions	Ratings	Unit
I _O	DC output current	3-phase fullwave rectified, T _j =104°C	30	A
I _{TSM} , I _{FSM}	Surge (non-repetitive) current	One half cycle at 60Hz, peak value	300	A
I ² t	I ² t for fusing	Value for one cycle of surge current	3.8 × 10 ²	A ² s
dI/dt	Critical rate of rise of on-state current	V _D =1/2V _{DRM} , I _G =0.5A, T _j =125°C	100	A/μs
P _{GM}	Peak gate power dissipation		5.0	W
P _{G (AV)}	Average gate power dissipation		0.5	W
V _{FGM}	Peak gate forward voltage		10	V
V _{RGM}	Peak gate reverse voltage		5.0	V
I _{FGM}	Peak gate forward current		2.0	A
T _j	Junction temperature		-40~125	°C
T _{stg}	Storage temperature		-40~125	°C
V _{iso}	Isolation voltage	Charged part to case	2500	V
—	Mounting torque	Main terminal screw M5	1.47~1.96	N·m
			15~20	kg·cm
		Mounting screw M5	1.47~1.96	N·m
	Weight	Typical value	15~20	kg·cm
			310	g

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{RRM}	Repetitive peak reverse current	T _j =125°C, V _{RRM} applied	—	—	4.0	mA
I _{DRM}	Repetitive peak of off-state	T _j =125°C, V _{DRM} applied	—	—	4.0	mA
V _{TM} , V _{FM}	current	T _j =125°C, I _{TM} =I _{FM} =75A, instantaneous meas.	—	—	1.5	V
dV/dt	Forward voltage	T _j =125°C, V _b =2/3V _{DRM}	500	—	—	V/μs
V _{GT}	Critical rate of rise of off-state voltage	T _j =25°C, V _d =6V, R _L =2Ω	—	—	2.0	V
V _{GD}	Gate trigger voltage	T _j =125°C, V _d =1/2V _{DRM}	0.25	—	—	V
I _{GT}	Gate non-trigger voltage	T _j =25°C, V _d =6V, R _L =2Ω	10	—	50	mA
R _{th (j-o)}	Gate trigger current	Junction to case (per 1/6 module)	—	—	1.8	°C/W
R _{th (c-f)}	Thermal resistance	Case to fin, Conductive grease applied (per 1/6 module)	—	—	0.36	°C/W
—	Contact thermal resistance Insulation resistance	Measured with a 500V megohmmeter between main terminal and case	10	—	—	MΩ

Note: Items of the above table applies to the Thyristor part and the Diode part as circled in the following tables.

MAXIMUM RATINGS

Item	V _{RRM}	V _{RSM}	V _R (DC)	V _{DRM}	V _{DSDM}	V _D (DC)	I _T (RMS)	I _T (AV)	I _{SM}	I ² _t	di/dt
	I _F (RMS)	I _F (AV)	I _{FSM}								
Thyristor	○	○	○	○	○	○	○	○	○	○	○
Diode	○	○	○	—	—	—	○	○	○	○	—

Item	P _{GM}	P _G (AV)	V _{FGM}	I _{FGM}	T _j	T _{stg}
Thyristor	○	○	○	○	○	○
Diode	—	—	—	—	○	○

ELECTRICAL CHARACTERISTICS

Item	I _{RRM}	I _{DRM}	V _{TM}	dv/dt	V _{GT}	V _{GD}	I _{GT}	R _{th} (j-c)	R _{th} (c-f)
			V _{FM}						
Thyristor	○	○	○	○	○	○	○	○	○
Diode	○	—	○	—	—	—	—	○	○

PERFORMANCE CURVES